

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



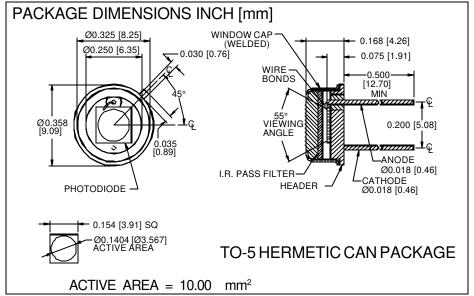




PHOTONIC DETECTORS INC.

Silicon Photodiode, Near I.R. Photovoltaic Type PDI-V106-F





FEATURES

Low noise

- Match to I.R. emitters
- Hermetic package

DESCRIPTION

The PDI-V106-F is a silicon, PIN planar • I.R. pass visible rejection diffused photodiode with NIR pass, visible light rejection optical filter. Ideal for low noise photovoltaic NIR applications. Packaged in a hermetic TO-5 metal can with a flat window cap.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V BR	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-55	+100	∘C
То	Operating Temperature Range	-40	+80	∘C
Ts	Soldering Temperature*		+240	∘C
I _L	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- I.R. detector
- I.R. laser detector
- Photo-interrupters
- Industrial controls

SPECTRALRESPONSE

RESPONSIVITY (A/W) 0.5 0.3 0.2 0.1 190 300 400 500 600 700 800 WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS		
Isc	Short Circuit Current	H = 100 fc, 2850 K	90	112		μA		
ΙD	Dark Current	$H = 0, V_R = 10 V$		300	500	pА		
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$.2	2		GΩ		
TC Rsh	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃		
CJ	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		1200		рF		
λrange	Spectral Application Range	Spot Scan	700		1100	nm		
λр	Spectral Response - Peak	Spot Scan		950		nm		
V _{BR}	Breakdown Voltage	I = 10 μμΑ	30	50		V		
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		1.0x10 ⁻¹⁴		W/√ _{Hz}		
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		800		nS		